2SB649, 2SB649A

Silicon PNP Epitaxial

HITACHI

Application

Low frequency power amplifier complementary pair with 2SD669/A

Outline

TO-126 MOD

1. Emitter
2. Collector
3. Base

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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings		Unit
		2SB649	2SB649A	
Collector to base voltage	V_{CBO}	–180	–180	V
Collector to emitter voltage	V_{CEO}	–120	–160	V
Emitter to base voltage	V_{EBO}	–5	–5	V
Collector current	I_C	–1.5	–1.5	A
Collector peak current	$I_{C(peak)}$	–3	–3	A
Collector power dissipation	P_C	1	1	W
	P_C*[1]	20	20	W
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	–55 to +150	–55 to +150	°C

Note: 1. Value at T_C = 25°C

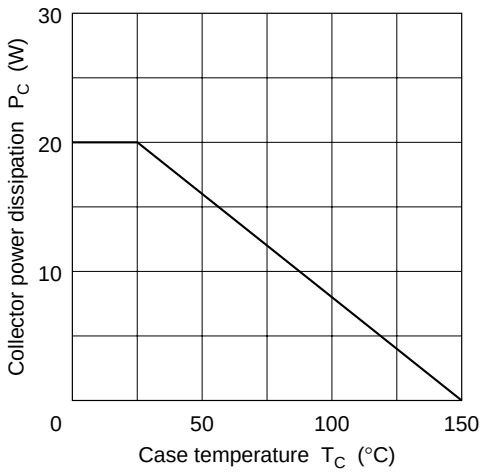
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SB649			2SB649A			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	–180	—	—	–180	—	—	V	I_C = –1 mA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	–120	—	—	–160	—	—	V	I_C = –10 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	–5	—	—	–5	—	—	V	I_E = –1 mA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	–10	—	—	–10	µA	V_{CB} = –160 V, I_E = 0
DC current transfer ratio	h_{FE1}*[1]	60	—	320	60	—	200		V_{CE} = –5 V, I_C = –150 mA
	h_{FE2}	30	—	—	30	—	—		V_{CE} = –5 V, I_C = –500 mA*[2]
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	–1	—	—	–1	V	I_C = –500 mA, I_B = –50 mA
Base to emitter voltage	V_{BE}	—	—	–1.5	—	—	–1.5	V	V_{CE} = –5 V, I_C = –150 mA
Gain bandwidth product	f_T	—	140	—	—	140	—	MHz	V_{CE} = –5 V, I_C = –150 mA
Collector output capacitance	Cob	—	27	—	—	27	—	pF	V_{CB} = –10 V, I_E = 0, f = 1 MHz

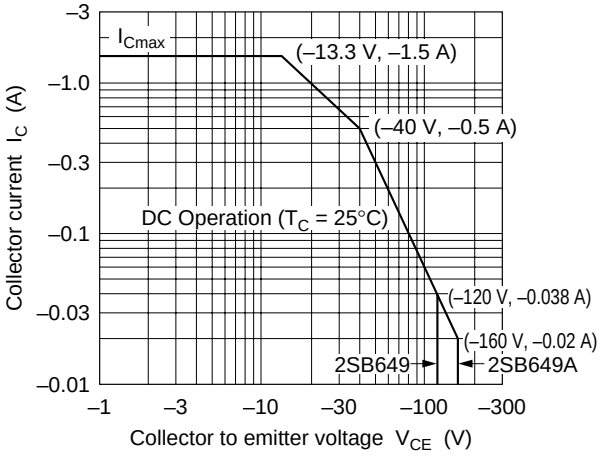
Notes: 1. The 2SB649 and 2SB649A are grouped by h_{FE1} as follows.
2. Pulse test

	B	C	D
2SB649	60 to 120	100 to 200	160 to 320
2SB649A	60 to 120	100 to 200	—

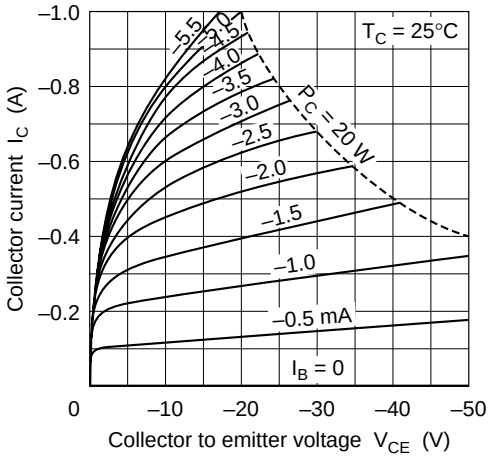
Maximum Collector Dissipation Curve



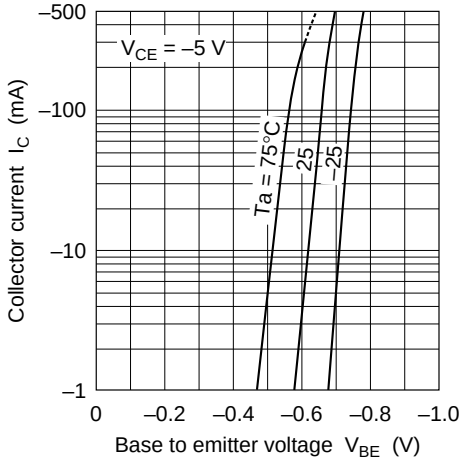
Area of Safe Operation



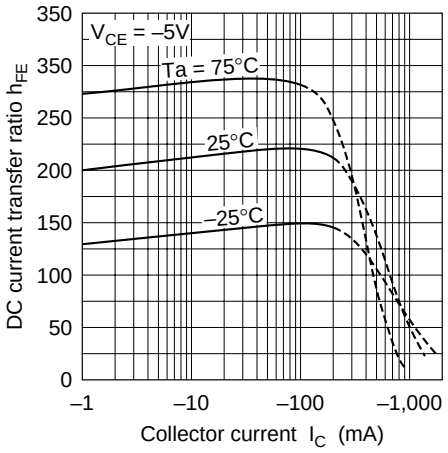
Typical Output Characteristics



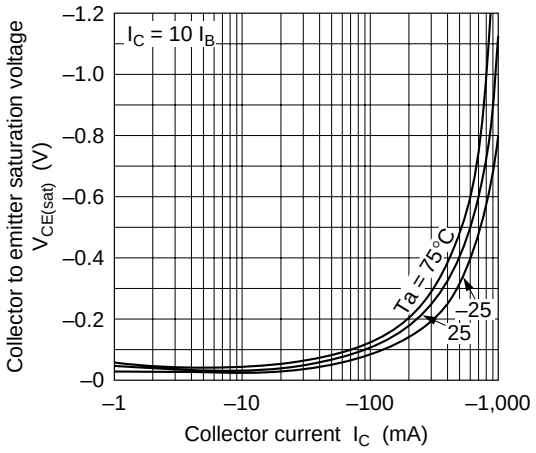
Typical Transfer Characteristics



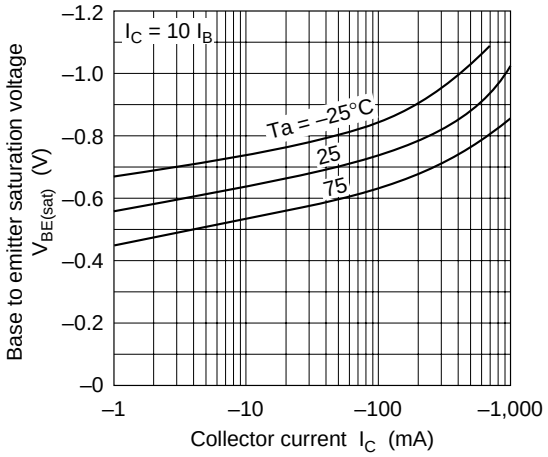
DC Current Transfer Ratio vs. Collector Current



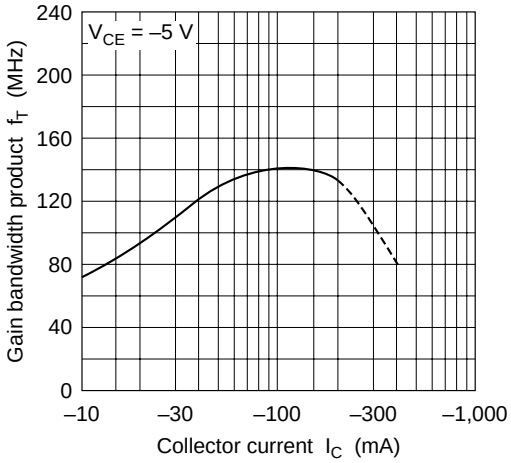
Collector to Emitter Saturation Voltage vs. Collector Current



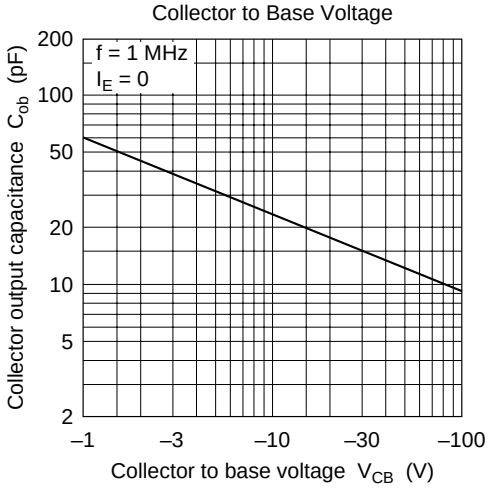
Base to Emitter Saturation Voltage vs. Collector Current



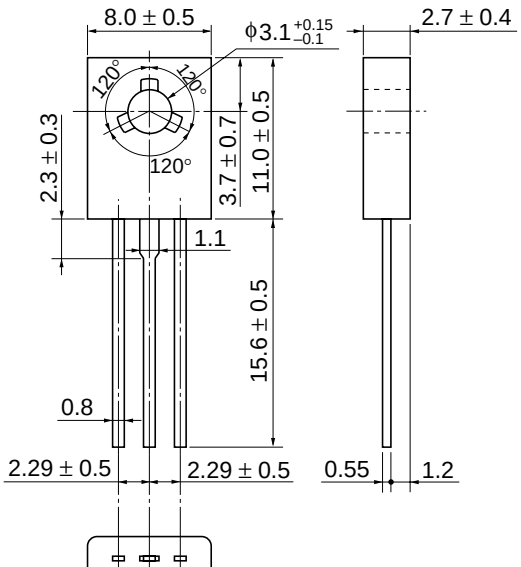
Gain Bandwidth Product vs. Collector Current

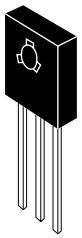


Collector Output Capacitance vs.
Collector to Base Voltage



Unit: mm


8.0 ± 0.5
ϕ3.1 +0.15 −0.1
2.7 ± 0.4
120°
120°
120°
2.3 ± 0.3
3.7 ± 0.7
11.0 ± 0.5
1.1
15.6 ± 0.5
0.8
2.29 ± 0.5
2.29 ± 0.5
0.55
1.2



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